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| Descrizione fisica      | 1 online resource (201 p.)   |
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| Altri autori (Persone)  | FisherD. J   |
| Disciplina              | 669.95   |
| Soggetti                | Physical metallurgy<br>Diffusion<br>Solids - Defects   |
| Lingua di pubblicazione | Inglese  |
| Formato                 | Materiale a stampa   |
| Livello bibliografico   | Monografia   |
| Note generali           | Description based upon print version of record.  |
| Nota di bibliografia    | Includes bibliographical references and indexes.   |
| Nota di contenuto       | HgCdTe System - Reference Guide; Table of Contents; Abstracts  |
| Sommario/riassunto      | This system, consisting of compositions lying between the end-members, CdTe and HgTe, constitutes perhaps the third most important semiconductor after Si and GaAs. Its importance stems from the ability to tailor the band-gap precisely between that (1.5eV) of the semiconductor, CdTe, and the zero value of the semi-metal, HgTe; giving, in particular, one of the most versatile infra-red detectors known. The intermediate compositions also benefit from the usual mechanisms which improve the mechanical properties of alloys. As an aid to those working on this system, this volume summarizes known diff |